



MT5LC1008
128K x 8 SRAM

SRAM

128K x 8 SRAM

LOW VOLTAGE WITH OUTPUT
ENABLE

FEATURES

- All I/O pins are 5V tolerant
- High speed: 15, 17, 20, 25, 35 and 45ns
- High-performance, low-power, CMOS double-metal process
- Single +3.3V $\pm 0.3V$ power supply
- Easy memory expansion with $\overline{CE1}$, CE2 and \overline{OE} options
- All inputs and outputs are TTL-compatible
- Fast \overline{OE} access time: 8ns
- Complies to JEDEC low-voltage TTL standards

OPTIONS

- Timing
 - 15ns access -15
 - 17ns access -17
 - 20ns access -20
 - 25ns access -25
 - 35ns access -35
 - 45ns access -45
- Packages
 - Plastic DIP (400 mil) None
 - Plastic SOJ (400 mil) DJ
 - Plastic SOJ (300 mil) SJ
- 2V data retention
 - L
 - 2V data retention, low power LP
- Temperature
 - Commercial (0°C to +70°C) None
 - Industrial (-40°C to +85°C) IT
 - Automotive (-40°C to +125°C) AT
 - Extended (-55°C to +125°C) XT
- Part Number Example: MT5LC1008DJ-35 LP

MARKING

NOTE: Not all combinations of operating temperature, speed, data retention and low power are necessarily available. Please contact the factory for availability of specific part number combinations.

GENERAL DESCRIPTION

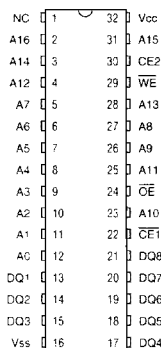
The MT5LC1008 is organized as a 131,072 x 8 SRAM using a four-transistor memory cell with a high-speed, low-power CMOS process. Micron SRAMs are fabricated using double-layer metal, double-layer polysilicon technology.

For flexibility in high-speed memory applications, Micron offers dual chip enables ($\overline{CE1}$, CE2). This enhancement can place the outputs in High-Z for additional flexibility in system design.

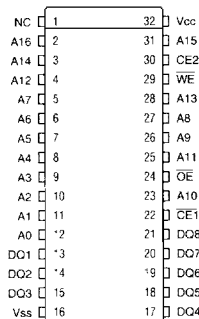
Writing to these devices is accomplished when write enable (\overline{WE}) and $\overline{CE1}$ inputs are both LOW and CE2 is

PIN ASSIGNMENT (Top View)

32-Pin DIP (SA-6)



32-Pin SOJ (SD-4) (SD-5)



3.3 VOLT SRAM

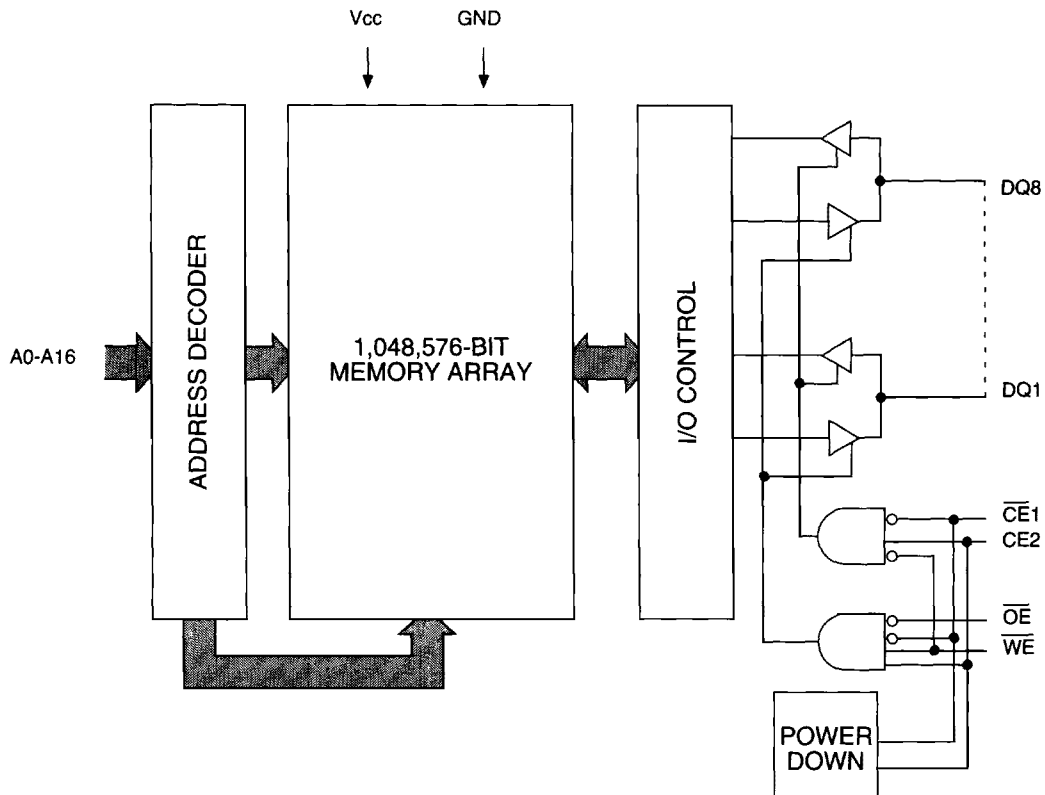
HIGH. Reading is accomplished when \overline{WE} and CE2 remain HIGH and $\overline{CE1}$ goes LOW. The device offers reduced power standby modes when disabled. These modes allow system designers to meet low standby power requirements.

The "LP" version provides a reduction in both CMOS standby current (I_{SB2}) and TTL standby current (I_{SB1}) over the standard part. This is achieved through the use of gated inputs on the \overline{WE} , \overline{OE} and address lines. The gated inputs also facilitate the design of battery-backed systems where the designer needs to protect against inadvertent battery current drain during power-down, when inputs may be at undefined levels.

All devices operate from a single +3.3V power supply and all inputs and outputs are fully TTL-compatible and 5V tolerant. These low-voltage parts are ideal for mixed 3.3V and 5V systems.

FUNCTIONAL BLOCK DIAGRAM

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TRUTH TABLE

MODE	\overline{OE}	$\overline{CE1}$	$CE2$	\overline{WE}	DQ	POWER
STANDBY	X	H	X	X	HIGH-Z	STANDBY
STANDBY	X	X	L	X	HIGH-Z	STANDBY
READ	L	L	H	H	Q	ACTIVE
NOT SELECTED	H	L	H	H	HIGH-Z	ACTIVE
WRITE	X	L	H	L	D	ACTIVE

MICRON**MT5LC1008
128K x 8 SRAM****ABSOLUTE MAXIMUM RATINGS***

Voltage on V _{CC} Supply Relative to V _{SS}	-0.5V to +4.6V
V _{IN}	-0.5V to +6.0V
Storage Temperature (plastic)	-55°C to +150°C
Power Dissipation	1W
Short Circuit Output Current	50mA

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

ELECTRICAL CHARACTERISTICS AND RECOMMENDED DC OPERATING CONDITIONS(0°C ≤ T_A ≤ 70°C; V_{CC} = 3.3V ±0.3V)

DESCRIPTION	CONDITIONS	SYMBOL	MIN	MAX	UNITS	NOTES
Input High (Logic 1) Voltage		V _{IH}	2.0	5.5	V	1, 2
Input Low (Logic 0) Voltage		V _{IL}	-0.3	0.8	V	1, 2
Input Leakage Current	0V ≤ V _{IN} ≤ V _{CC}	I _{LJ}	-1	1	μA	
Output Leakage Current	Output(s) disabled 0V ≤ V _{OUT} ≤ V _{CC}	I _{LO}	-1	1	μA	
Output High Voltage	I _{OH} = -4.0mA	V _{OH}	2.4		V	1
Output Low Voltage	I _{OL} = 8.0mA	V _{OL}		0.4	V	1
Supply Voltage		V _{CC}	3.0	3.6	V	1

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DESCRIPTION	CONDITIONS	SYMBOL	VER	MAX						UNITS	NOTES
				-15	-17	-20	-25	-35	-45		
Power Supply Current: Operating	CE1 ≤ V _{IL} AND CE2 ≥ V _{IH} ; V _{CC} = MAX; outputs open f = MAX = 1/t _{RC}	I _{CC}	ALL	85	75	65	55	45	40	mA	3, 15
Power Supply Current: Standby	CE1 ≤ V _{IH} AND CE2 ≥ V _{IL} ; V _{CC} = MAX; outputs open f = MAX = 1/t _{RC}	I _{SB1}	STD, L	20	18	14	12	8	6	mA	15, 16
			LP	500	500	500	500	500	500	μA	
	CE1 ≥ V _{CC} - 0.2V or CE2 ≤ V _{SS} + 0.2V V _{CC} = MAX V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ V _{SS} + 0.2V	I _{SB2}	STD, L	300	300	300	300	300	300	μA	15, 17
			LP	100	100	100	100	100	100	μA	

CAPACITANCE

DESCRIPTION	CONDITIONS	SYMBOL	MAX	UNITS	NOTES
Input Capacitance	T _A = 25°C; f = 1 MHz V _{CC} = 3.3V	C _I	8	pF	4
Output Capacitance		C _O	8	pF	4



ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS

(Note 5, 14) (0°C ≤ T_A ≤ 70°C; V_{CC} = 3.3V ±0.3V)

3.3 VOLT SRAM

DESCRIPTION	SYM	-15		-17		-20		-25		-35		-45		UNITS	NOTES
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
READ Cycle															
READ cycle time	¹ RC	15		17		20		25		35		45		ns	
Address access time	¹ AA		15		17		20		25		35		45	ns	
Chip Enable access time	¹ ACE		15		17		20		25		35		45	ns	
Output hold from address change	¹ OH	3		3		3		5		5		5		ns	
Chip Enable to output in Low-Z	¹ LZCE	5		5		3		5		5		5		ns	7
Chip disable to output in High-Z	¹ HZCE		6		7		8		10		15		18	ns	6, 7
Chip Enable to power-up time	¹ PU	0		0		0		0		0		0		ns	
Chip disable to power-down time	¹ PD		15		17		20		25		35		45	ns	
Output Enable access time	¹ AOE		5		5		4		8		12		15	ns	
Output Enable to output in Low-Z	¹ LZOE	0		0		0		0		0		0		ns	
Output disable to output in High-Z	¹ HZOE		5		5		4		10		12		15	ns	6
WRITE Cycle															
WRITE cycle time	¹ WC	15		17		20		25		35		45		ns	
Chip Enable to end of write	¹ CW	10		12		12		15		20		25		ns	
Address valid to end of write	¹ AW	10		12		12		15		20		25		ns	
Address setup time	¹ AS	0		0		0		0		0		0		ns	
Address hold from end of write	¹ AH	0		0		0		0		0		0		ns	
WRITE pulse width	¹ WP1	9		12		12		15		20		25		ns	
WRITE pulse width	¹ WP2	12		13		15		15		20		25		ns	
Data setup time	¹ DS	7		8		8		10		15		20		ns	
Data hold time	¹ DH	0		0		0		0		0		0		ns	
Write disable to output in Low-Z	¹ LZWE	3		3		3		5		5		5		ns	7
Write Enable to output in High-Z	¹ HZWE		6		7		8		10		15		18	ns	6, 7

AC TEST CONDITIONS

Input pulse levels	V _{SS} to 3.0V
Input rise and fall times	3ns
Input timing reference levels	1.5V
Output reference levels	1.5V
Output load	See Figures 1 and 2

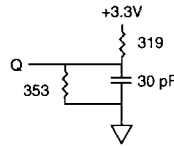


Fig. 1 OUTPUT LOAD EQUIVALENT

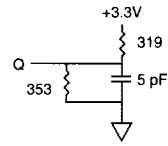


Fig. 2 OUTPUT LOAD EQUIVALENT

NOTES

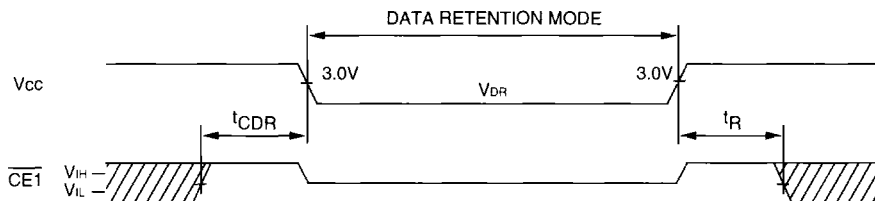
- All voltages referenced to V_{SS} (GND).
- Overshoot: V_{IH} ≤ +6.0V for t ≤ ¹RC/2
Undershoot: V_{IL} ≥ -2.0V for t ≤ ¹RC/2
Power-up: V_{IH} ≤ +6.0V and V_{CC} ≤ 3.1V for t ≤ 200msec.
- I_{CC} is dependent on output loading and cycle rates.
- This parameter is sampled.
- Test conditions as specified with the output loading as shown in Fig. 1 unless otherwise noted.
- ¹HZCE, ¹HZOE and ¹HZWE are specified with CL = 5pF as in Fig. 2. Transition is measured ±200mV from steady state voltage.
- At any given temperature and voltage condition, ¹HZCE is less than ¹LZCE and ¹HZWE is less than ¹LZWE.
- WE is HIGH for READ cycle.
- Device is continuously selected. All chip enables and output enables are held in their active state.
- Address valid prior to, or coincident with, latest occurring chip enable.
- ¹RC = Read Cycle Time.
- CE2 timing is the same as CE1 timing. The wave form is inverted.
- Chip enable and write enable can initiate and terminate a WRITE cycle.
- Contact Micron for IT/AT/XT timing and current specifications; they may differ from the commercial temperature range specifications shown in this data sheet.
- Typical values are measured at 3.3V, 25°C and 25ns cycle time.
- One chip enable must be inactive; the other may be ≥ V_{IH} or ≤ V_{IL}.
- One chip enable must be inactive; the other may be ≤ V_{SS} +0.2 or ≥ V_{CC} -0.2.
- Typical currents are measured at 25°C.

3.3 VOLT SRAM

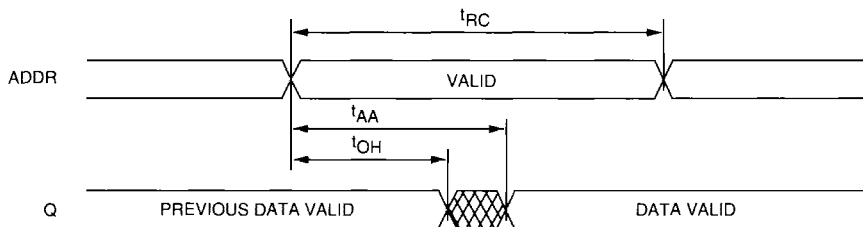
DATA RETENTION ELECTRICAL CHARACTERISTICS (L and LP versions only)

DESCRIPTION	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
V _{CC} for Retention Data		V _{DR}	2			V	
Data Retention Current L version	<u>CE1</u> ≥ V _{CC} -0.2V or <u>CE2</u> ≤ V _{SS} +0.2V Other inputs: V _{IN} ≥ V _{CC} -0.2V or V _{IN} ≤ V _{SS} +0.2V V _{CC} = 2V	I _{CCDR}		TBD	50	μA	17, 18
Data Retention Current LP version	<u>CE1</u> ≥ V _{CC} -0.2V or <u>CE2</u> ≤ V _{SS} +0.2V V _{CC} = 2V	I _{CCDR}		TBD	50	μA	17, 18
Chip Deselect to Data Retention Time		¹ CDR	0			ns	4
Operation Recovery Time		¹ R	¹ RC			ns	4, 11

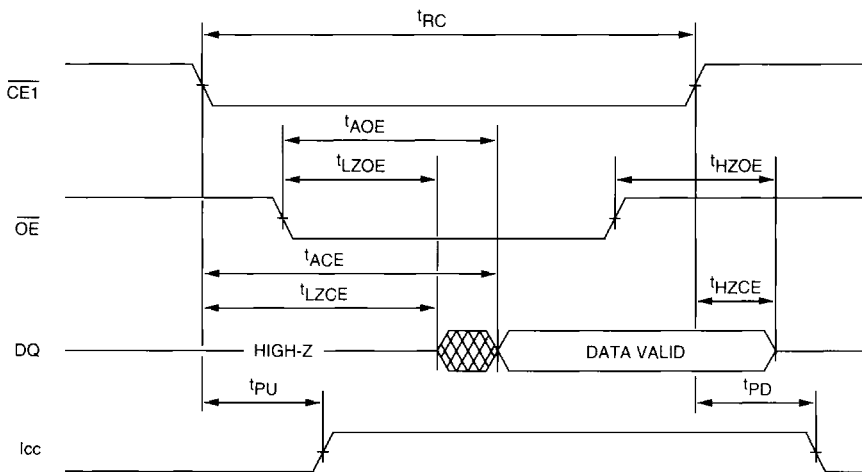
LOW V_{CC} DATA RETENTION WAVEFORM ¹²



READ CYCLE NO. 1 ^{8,9}



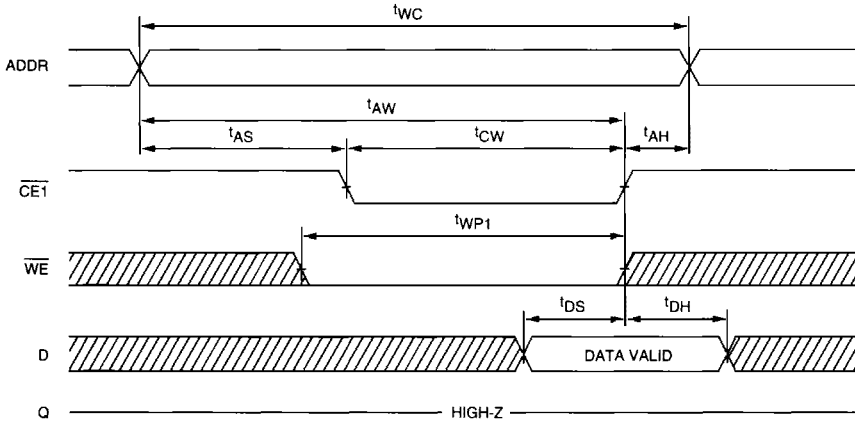
READ CYCLE NO. 2 ^{7, 8, 10, 12}



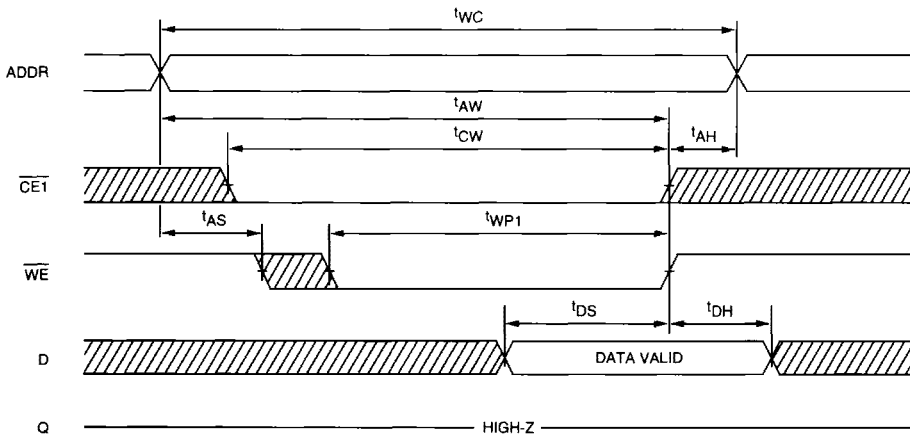
DON'T CARE
 UNDEFINED



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WRITE CYCLE NO. 1¹²
(Chip Enable Controlled)



WRITE CYCLE NO. 2^{12, 13}
(Write Enable Controlled)

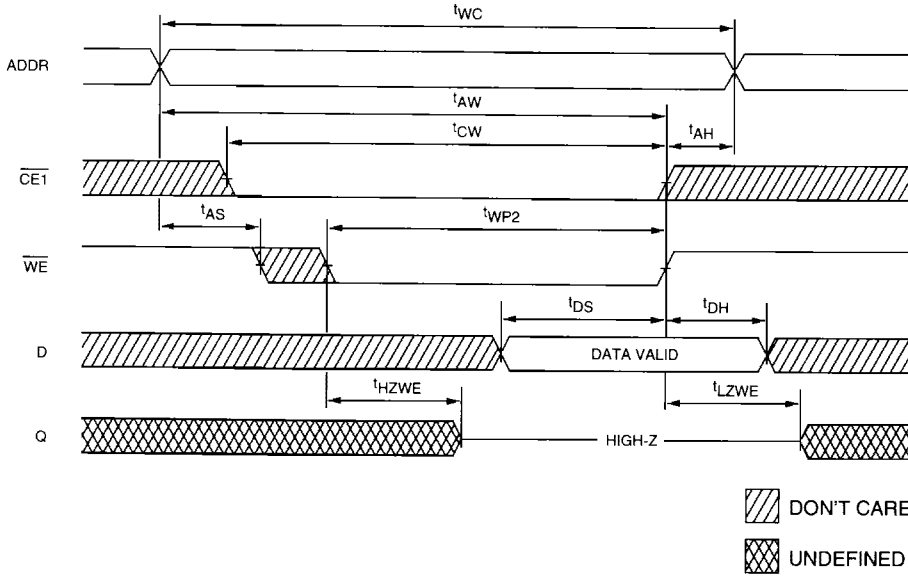


 DON'T CARE
 UNDEFINED

NOTE: Output enable (\overline{OE}) is inactive (HIGH).

WRITE CYCLE NO. 3 7, 12, 13
(Write Enable Controlled)

3.3 VOLT SRAM



NOTE: Output enable (\overline{OE}) is active (LOW).